

# Hung-Wei Chen

## List of Publications by Year in descending order

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3  
papers

6  
citations

3311381

1  
h-index

2917675

2  
g-index

3  
all docs

3  
docs citations

3  
times ranked

2  
citing authors

#	ARTICLE	IF	CITATIONS
1	ESD Improvements on Power N-Channel LDMOS Devices by the Composite Structure of Super Junctions Integrated With SCRs in the Drain Side. IEEE Journal of the Electron Devices Society, 2020, 8, 864-872.	2.1	4
2	Drain Side Area-Modulation Effect of Parasitic Schottky Diode on ESD Reliability for High Voltage P-Channel Lateral-Diffused MOSFETs. IEEE Electron Device Letters, 2021, 42, 1512-1515.	3.9	2
3	Research on ESD Protection of Ultra-High Voltage nLDMOS Devices by Super-Junction Engineering in the Drain-Side Drift Region. IEEE Journal of the Electron Devices Society, 2021, 9, 763-773.	2.1	0